

IN THE CLAIMS

1. (Currently Amended) A semiconductor integrated circuit device, comprising:

an internal supply generating means for generating, from an external supply voltage that is externally input, an internal supply voltage at which a logic circuit is operated; and

a level shift means for shift a voltage amplitude level of a signal input to and output from said logic circuit,

wherein said internal supply generating means includes:

a high voltage supply generating unit for generating a high voltage internal power supply from a high voltage external power supply of said external supply voltage; and

a low voltage supply generating unit for generating a low voltage internal power supply from a low voltage external power supply of said external supply voltage,

in which a high voltage internal power supply and a low voltage internal power supply, generated from said high voltage supply generating unit and said low voltage supply

generating unit, are used as internal supply voltages and are supplied to said logic circuit.

2. (Canceled).

3. (Currently Amended) The semiconductor integrated circuit device according to claim 21,

wherein said high voltage supply generating unit includes:

a first voltage comparing unit comparing voltage levels of a first reference voltage and a high voltage internal power supply generated by said high voltage supply generating unit, and outputting a first internal control signal changing its voltage in accordance with a difference between the voltage levels; and

a first internal supply generating unit having a structure in which a plurality of power supply transistors are connected in parallel between said high voltage external power supply and said high voltage internal power supply and a first internal control signal, output by said first supply comparing unit, is input to each gate of said plurality of power supply

transistors, and driving said plurality of power supply transistors in accordance with said first internal control signal to generate said high voltage internal power supply, and

wherein said low voltage supply generating unit includes:

a second voltage comparing unit comparing voltage levels of a second reference voltage and a low voltage internal power supply generated by said low voltage supply generating unit, and outputting a second internal control signal changing its voltage in accordance with a difference between the voltage levels; and

a second internal supply generating unit having a structure in which a plurality of power supply transistors are connected in parallel between said low voltage external power supply and said low voltage internal power supply and said second internal control signal, output by said second voltage comparing unit, is input to each gate of said plurality of power supply transistors, and driving said plurality of power supply transistors in accordance with said second internal control signal to generate said low voltage internal power supply.

4. (Currently Amended) The semiconductor integrated circuit device according to claim ~~21~~,
wherein said high voltage supply generating unit

includes:

a first voltage comparing unit comparing voltage levels of a first reference voltage and a high voltage internal power supply generated by said high voltage supply generating unit, and outputting a first internal control signal changing its voltage in accordance with a difference between the voltage levels; and

a first internal supply controlling unit provided with a first duty control circuit, which generates a pulse signal having an arbitrary duty ratio in accordance with a first internal control signal output from said first voltage comparing unit, and with a plurality of power supply transistors, which are connected in parallel between said high voltage external power supply and said high voltage internal power supply and to each gate of which a pulse signal, output from said first duty control circuit,

in which said first internal supply controlling unit generates said high voltage internal power supply by driving

said plurality of power supply transistors in accordance with said pulse signal, and

wherein said low voltage supply generating unit includes:

a second voltage comparing unit comparing voltage levels of a second reference voltage and a low voltage internal power supply generated by said low voltage supply generating unit, and outputting a second internal control signal changing its voltage in accordance with a difference between the voltage levels; and

a second internal supply controlling unit provided with a second duty control circuit, which generates a pulse signal having an arbitrary duty ratio in accordance with a second internal control signal output from said second voltage comparing unit, and with a plurality of power supply transistors, which are connected in parallel between said low voltage external power supply and said low voltage internal power supply and to each gate of which a pulse signal, output from said second duty control circuit, is input,

in which said second internal supply controlling unit generates said low voltage internal power supply by driving

said plurality of power supply transistors in accordance with said pulse signal.

5. (Original) The semiconductor integrated circuit device according to claim 3,

wherein said first and second voltage comparing units stopping said plurality of power supply transistors in accordance with a input setting signal, and electrically separate said high voltage external power supply and said high voltage internal power supply, as well as said low voltage external power supply and said low voltage internal power supply, respectively.

6. (Original) The semiconductor integrated circuit device according to claim 5,

wherein said high voltage supply generating unit includes:

a first transistor connected between said high voltage internal power supply and said high voltage external power supply, and conducted when said first voltage comparing unit electrically separates said high voltage external power supply

and said high voltage internal power supply in accordance with a control signal, and

wherein said low voltage supply generating unit includes:

a second transistor connected between said low voltage internal power supply and said low voltage external power supply, and conducted when said second voltage comparing unit electrically separates said low voltage external power supply and said low voltage internal power supply in accordance with a control signal.

7. (Original) The semiconductor integrated circuit device according to claim 1,

wherein an ESD protection device, serving as a supply capacitor, is provided between internal supply voltages generated by said internal supply generating unit.

8. (Original) The semiconductor integrated circuit device according to claim 1,

wherein each of said first internal supply controlling unit, said second internal supply controlling unit, and said

ESD protection device is provided two or more in number, thereby being dispersedly disposed on a semiconductor chip.

9. (Currently Amended) The semiconductor integrated circuit device according to claim ~~21~~,
21,

wherein a reference voltage generating unit for generating said first and second reference voltages is provided.

10. (Original) The semiconductor integrated circuit device according to claim 1,

wherein said level shifter includes:

a first level shift unit shifting, into a signal amplitude of an external supply voltage level, a signal amplitude of an internal supply voltage level output from said logic circuit, and

a second level shift unit shifting, into a signal amplitude of an internal supply voltage level at which said logic circuit is operated, a signal amplitude of an external supply voltage level having been input externally.

11. (Currently Amended) An electronic system comprising:
a semiconductor integrated circuit device including an
internal supply voltage generating means for generating, from
an external supply voltage that is externally input, an
internal supply voltage at which a logic circuit is operated;
and

an electronic component mounting board for mounting said
semiconductor integrated circuit device,

wherein said internal supply voltage generating means
includes:

a high voltage supply generating unit generating a high
voltage internal power supply, from a high voltage external
power supply of an external supply voltage supplied through a
power supply wire formed on said electronic component mounting
board; and

a low voltage supply generating unit generating a low
voltage internal power supply, from a low voltage external
power supply of an external supply voltage supplied through a
power supply wire formed on said electronic component mounting
board,

in which said high voltage internal power supply and said low voltage internal power supply, generated by said high voltage supply generating unit and said low voltage supply generating unit, are used as internal supply voltages and are supplied to said logic circuit.

12. (Canceled).

13. (Currently Amended) The electronic system according to claim-~~12~~11,

wherein said high voltage supply generating unit includes:

a first voltage comparing unit comparing voltage levels of a first reference voltage and a high voltage internal power supply generated by said high voltage supply generating unit, and outputting a first internal control signal changing its voltage in accordance with a difference between the voltage levels; and

a first internal supply controlling unit having a structure in which a plurality of power supply transistors are connected in parallel between said high voltage external power

supply and said high voltage internal power supply and said high voltage internal power supply and a first internal control signal, output by said first voltage comparing unit, is input to each gate of said plurality of power supply transistors, and driving said plurality of power supply transistors in accordance with said first internal control signal to generate said high voltage internal power supply, and

wherein said low voltage supply generating unit includes:

a second voltage comparing unit comparing voltage levels of a second reference voltage and a low voltage internal power supply generated by said low voltage supply generating unit, and outputting a second internal control signal changing its value in accordance with a difference between the voltage levels; and

a second internal supply controlling unit having a structure in which a plurality of power supply transistors are connected in parallel between said low voltage external power supply and said low voltage internal power supply and said second internal control signal, output by said second voltage comparing unit, is input to each gate of said plurality of

power supply transistors, and driving said plurality of power supply transistors in accordance with said second internal control signal to generate said low voltage internal power supply.